

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN MPA-PWR/06/2234 Notification Date 12/22/2006

Silicon Line Change for Bipolar devices

PWR - PWR BIP/ IGBT/ RF

Table 1. Change Identification

Product Identification (Product Family/Commercial Product)	2SD2012 - MJE521 - BD435 - BD437
Type of change	Waferfab technology change
Reason for change	To improve performances
Description of the change	Planar Base Island technology ready to replace the mature Epibase technology in order to align our products to the actual Market. Feature: Improved hFE linearity and Higher fT frequency benefit: Better performances in switching and linear application. The line BA17 will replace the old ones B541 and B542.
Product Line(s) and/or Part Number(s)	See attached
Description of the Qualification Plan	See attached
Change Product Identification	See "N" in additional info on P/N.
Manufacturing Location(s)	

Table 2. Change Implementation Schedule

Forecasted implementation date for change	18-Mar-2007
Forecasted availabillity date of samples for customer	14-Jan-2007
Forecasted date for STMicroelectronics change Qualification Plan results availability	18-Dec-2006
Estimated date of changed product first shipment	18-Mar-2007

47/.

Table 3. Change Responsibility

	Name	Signature	Date
Division Product Manager	Claudio Porto		Dec.18 ,06
Division Q.A. Manager	Giuseppe Falcone		Dec.18 ,06
Division Marketing Manager	Alfio Lanzafame		Dec.18 ,06

Table 4. List of Attachments

Customer Part numbers list	
Qualification Plan results	

Customer Acknowledgement of Receipt	PCN MPA-PWR/06/2234
Please sign and return to STMicroelectronics	Sales Office Notification Date 12/22/2006
□ Qualification Plan Denied	Name:
□ Qualification Plan Approved	Title:
	Company:
□ Change Denied	Date:
□ Change Approved	Signature:
Remark	

A7/.



Date:	December '06
No	20/2006

Reliability evaluation on BA17 for

Silicon Line Change on Bipolar devices

ISSUED BY	RELIABILITY DEPARTMENT	Page 1 of 11
-----------	---------------------------	--------------



Date:	December '06
No	20/2006

Table of Contents

1.	Introduction	pg.	3
2.	Test vehicles	pg.	4
3.	Failure Criteria	pg.	5
4.	Evaluation plan and results	pg.	6
5.	Appendixes		
	- Technological Characteristics	pg.	8
	- Reliability Test Description	pg.	10

ISSUED BY	RELIABILITY DEPARTMENT	Page 2 of 11
-----------	---------------------------	--------------



Date:	December '06
No	20/2006

Introduction

This report aims at the internal qualification of the BA17 Silicon Line for Bipolar devices.

The Qualification Reliability test trials have been performed in ST Catania Site.

The evaluation results meet ST products qualification targets, therefore the Silicon Line BA17 for Bipolar devices is qualified.

ISSUED BY	RELIABILITY DEPARTMENT	Page 3 of 11
-----------	---------------------------	--------------



Date:	December '06
No	20/2006

Test Vehicles:

Product LineSales TypePackageBA172SD2012TO-220FPBA17MJE521SOT-32



Date:	December '06
No	20/2006

Failure Criteria:

A failed component is a device which becomes inoperative during the test or it fails on meeting the end limits foreseen in the device specification, for one or more than the parameters here below reported

Power Bipolar Main Parameters

Collector Leakage Current (Icbo or Iceo or Ices, etc...) Emitter Leakage (Iebo) HFE, Vcesat, Vbesat, Vf Breakdown Voltage (BVcbo, BVceo, Vbces, Bvebo)



Date:	December '06
No	20/2006

Reliability Evaluation Plan and results

D.U.T.: 2SD2012 Line: BA17 Package: TO-220FP

Test	Conditions	S.S.	Requirement	Results
H.T.S.	TA=150℃	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
T.H.B.	TA=85℃ - RH=85% Vbias= 50V	77 x 1 Lot		No parameter deviation out of spec. limits at 1000 hours.
H.T.R.B.	T.A.= 150℃ Vces = 48 V	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
PRESSURE POT	TA=121℃ - PA=2Atm	77 x 1 Lot		No parameter deviation out of spec. limits at 96 hours.
THERMAL FATIGUE	ΔTC=105℃ - Pd=4.75W	77x1 Lot	Parameter deviation within spec. limits at 10k cycles.	No failure up to 10Kcy.
THERMAL CYCLES AIR TO AIR	TA=-65℃ TO 150℃ 1 HOUR / CYCLE	77 x 1 Lot		No parameter deviation out of spec. limits at 500 cy

ISSUED BY	RELIABILITY DEPARTMENT	Page 6 of 11
-----------	---------------------------	--------------



Date:	December '06
No	20/2006

Reliability Evaluation Plan and results

D.U.T.: MJE521 Line: BA17 Package: SOT-32

Test	Conditions	S.S.	Requirement	Results
H.T.S.	TA=150℃	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
T.H.B.	TA=85℃ - RH=85% Vbias= 24V	77 x 1 Lot	Parameter deviation within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
H.T.R.B.	T.A.= 150℃ Vces = 32 V	77 x 1 Lot		No parameter deviation out of spec. limits at 1000 hours.
PRESSURE POT	TA=121℃ - PA=2Atm	77 x 1 Lot	Parameter deviation within spec. limits at 96 hours.	No parameter deviation out of spec. limits at 96 hours.
THERMAL FATIGUE	ΔTC=105 ℃ - Pd= 3W	77x1 Lot	Parameter deviation within spec. limits at 10k cycles.	No failure up to 10Kcy.
THERMAL CYCLES AIR TO AIR	TA=-65℃ TO 150℃ 1 HOUR / CYCLE	77 x 1 Lot	1	No parameter deviation out of spec. limits at 500 cy

ISSUED BY	RELIABILITY DEPARTMENT	Page 7 of 11
-----------	---------------------------	--------------



Date:	December '06
No	20/2006

Technological Characteristics

D.U.T.: 2SD2012 Line: BA17 Package: TO-220FP

DIE		Planar NPN Silicon Al/Si AuAs/Cr/Ni/Au	Passivation : Dimensions :	
DIE ATTACH	Soft Solder Pb/Sn/Ag	FRAME	Frame and lead material: Frame coating : Lead coating :	Row copper Nickel Plated Sn 100%
WIRE BOND	Ultrasonic	WIRE	Material : Diameter :	Al/Mg Base Al/Mg Emitter 5 mils Base 5 mils Emitter
SEALING	Molding	PACKAGING	Material :	Epoxy Resin

PRODUCTION PLACES: WAFER PROCESSING : SINGAPORE



Date:	December '06
No	20/2006

Technological Characteristics

D.U.T.: MJE521 Line: BA17 Package: SOT-32

DIE		Planar NPN Silicon Al/Si AuAs/Cr/Ni/Au	Passivation : Dimensions :	
DIE ATTACH	Soft Solder Pb/Sn/Ag	FRAME	Frame and lead material: Frame coating : Lead coating :	Row copper Nickel Plated Sn 100%
WIRE BOND	Ultrasonic	WIRE	Material : Diameter :	Al/Mg Base Al/Mg Emitter 5 mils Base 5 mils Emitter
SEALING	Molding	PACKAGING	Material :	Epoxy Resin

PRODUCTION PLACES: WAFER PROCESSING : SINGAPORE

ASSEMBLY LOCATION : INDIA / PHILIPPINES

Q.A. LOCATION : INDIA / PHILIPPINES

ISSUED BY	RELIABILITY DEPARTMENT	Page 9 of 11
-----------	---------------------------	--------------



Date:	December '06
No	20/2006

Reliability Test Description

High Temperature Reverse Bias (HTRB)

This test is performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and simultaneously reverse biased. The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, etc...

High Temperature Storage (HTS)

This stress test is performed to check the device life in a high temperature ambient. Specimens are put for a period of time inside a stove in free air. Detectable failure mechanisms are presence of contaminants and metal corrosion.

Thermal Cycles/Shocks

The purpose of this test is to determine the resistance of devices to exposure to extreme changes in temperature. Specimens are first placed in a suitable environment at a low temperature and then transferred to one at high temperature. Effects of thermal cycles/shocks include cracking of die, breaking of wire bonding, mechanical damage to the device case.

Temperature Humidity Bias (THB)

This test is performed to check the device life in a high humidity ambient. Specimens are subjected to a permanent bias in a climatic chamber in the presence of steam. Detectable failure mechanisms are metal corrosion and moulding defects.

ISSUED BY	RELIABILITY DEPARTMENT	Page 10 of 11
-----------	---------------------------	---------------



Date:	December '06
No	20/2006

Reliability Test Description (continued)

Pressure Pot

This test is performed in order to check device life in a high humidity ambient in an accelerated way. Specimens are subjected for a period of time inside an autoclave in the presence of steam and pressure. Detectable failure mechanism is metal corrosion.

Thermal Fatigue

This test is performed to demonstrate the quality and reliability of devices exposed to cyclic variation in electrical stress between "on" and "off" conditions and resultant cyclic variation in device and case temperatures (thermo-mechanical stress). The purpose of this test is to detect assembly defects: improper die-attach, bonding weakness and thermal mismatch among various components of the package.

ISSUED BY RELIABILITY DEPARTMENT Page 11 of 11
--

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZE REPRESENTATIVE OF ST,ST PRODUCTS ARE NOT DESIGNED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2006 STMicroelectronics - All rights reserved.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morroco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

